Continental Device India Pvt. Limited An IATF 16949, ISO9001 and ISO 14001 Certified Company **High Power NPN Silicon Power Transistors** 

20&30 AMPERES, 40&60 VOLTS, 150 WATTS

2N3771 2N3772 TO-3 Metal Can Package **RoHS compliant** 

**TO-3** 

FEATURES: Forward Biased Second Breakdown Current Capability

2N3771--  $I_{\text{S/b}}$  = 3.75 A dc @ V\_{CE}\, = 40 Vdc

 $2N3772 - I_{S/b} = 2.5 \text{ A dc} @ V_{CE} = 60 \text{ Vdc}$ 

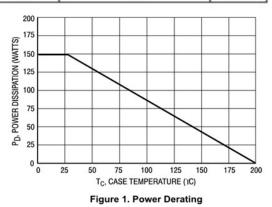
APPLICATIONS: Linear amplifiers, series pass regulators, and inductive switching applications.

ABSOLUTE	MAXIMUM	RATINGS (T	a = 25 °C)
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Rating	Symbol	2N3771	2N3772	Unit
Collector–Emitter Voltage	VCEO	40	60	Vdc
Collector-Emitter Voltage	VCEX	50	80	Vdc
Collector-Base Voltage	V <sub>CB</sub>	50	100	Vdc
Emitter-Base Voltage	VEB	5.0	7.0	Vdc
Collector Current — Continuous Peak	Ic	30 30	20 30	Adc
Base Current — Continuous Peak	IB	7.5 15	5.0 15	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	150 0.855		Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C

#### THERMAL CHARACTERISTICS

Characteristics	Symbol	2N3771, 2N3772	Unit
Thermal Resistance, Junction to Case	JC	1.17	°C/W











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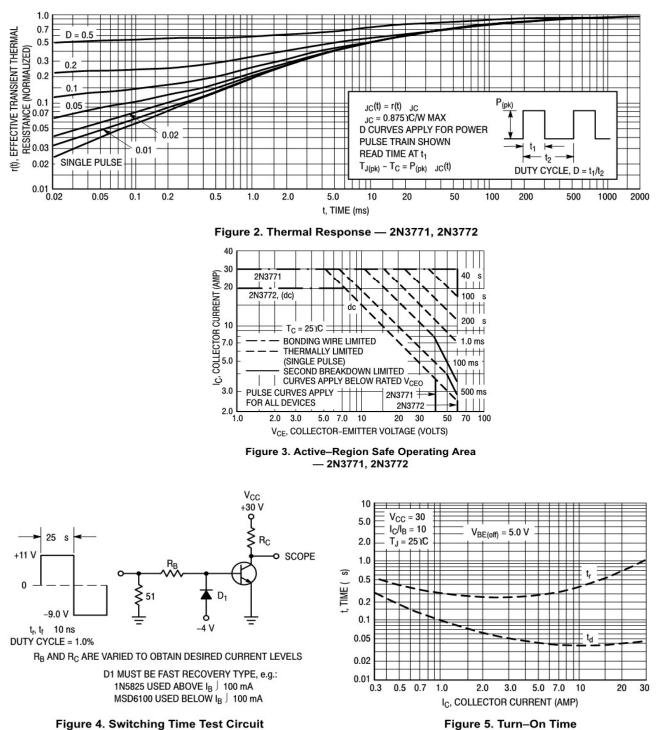
# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub>=25 ° C unless otherwise specified)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
*Collector-Emitter Sustaining Voltage (1)	2N3771	V <sub>CEO(sus)</sub>	40	_	Vdc
$(I_{C} = 0.2 \text{ Adc}, I_{B} = 0)$	2N3772	,	60	-	
Collector-Emitter Sustaining Voltage	2N3771	V <sub>CEX(sus)</sub>	50	_	Vdc
$(I_{C} = 0.2 \text{ Adc}, V_{EB(off)} = 1.5 \text{ Vdc}, R_{BE} = 100 \text{ Ohms})$	2N3772	0_0.000,	80	-	
Collector–Emitter Sustaining Voltage	2N3771	V <sub>CER(sus)</sub>	45	_	Vdc
(I <sub>C</sub> = 0.2 Adc, R <sub>BE</sub> = 100 Ohms)	2N3772		70	_	
*Collector Cutoff Current		I <sub>CEO</sub>			mAdd
$(V_{CE} = 30 \text{ Vdc}, I_B = 0)$	2N3771			10	
$(V_{CE} = 50 \text{ Vdc}, I_{B} = 0)$	2N3772			10	
$(V_{CE} = 25 \text{ Vdc}, I_B = 0)$					
*Collector Cutoff Current		ICEV			mAdo
$(V_{CE} = 50 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$	2N3771			2.0	
$(V_{CE} = 100 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$	2N3772			5.0	
$(V_{CE} = 45 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$	2N6257		_	4.0	
$(V_{CE} = 30 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 150^{\circ}\text{C})$	2N3771 2N3772		_	10	
(V <sub>CE</sub> = 45 Vdc, V <sub>EB(off)</sub> = 1.5 Vdc, T <sub>C</sub> = 150°C)	2113772		<u></u> 20	10	
*Collector Cutoff Current		I <sub>CBO</sub>			mAdo
$(V_{CB} = 50 \text{ Vdc}, I_{E} = 0)$	2N3771	ICBO		2.0	
$(V_{CB} = 100 \text{ Vdc}, I_E = 0)$	2N3772		_	5.0	
*Emitter Cutoff Current		I <sub>EBO</sub>			mAdo
$(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	2N3771	-EBO	11	5.0	
$(V_{BE} = 7.0 \text{ Vdc}, I_{C} = 0)$	2N3772			5.0	
ON CHARACTERISTICS					
DC Current Gain (1)		h <sub>FE</sub>			
(I <sub>C</sub> = 15 Adc, V <sub>CE</sub> = 4.0 Vdc)	2N3771		15	60	
$(I_{C} = 10 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$	2N3772		15	60	
$(I_{C} = 8.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$					
$(I_{C} = 30 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$	2N3771		5.0	_	
$(I_{C} = 20 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$	2N3772		5.0		
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>			Vdc
(I <sub>C</sub> = 15 Adc, I <sub>B</sub> = 1.5 Adc)	2N3771			2.0	
(I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 1.0 Adc)	2N3772			1.4	
$(I_{C} = 30 \text{ Adc}, I_{B} = 6.0 \text{ Adc})$	2N3771		_	4.0	
(I <sub>C</sub> = 20 Adc, I <sub>B</sub> = 4.0 Adc)	2N3772			4.0	
Base–Emitter On Voltage		V <sub>BE(on)</sub>			Vdc
$(I_{C} = 15 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$	2N3771			2.7	
$(I_{C} = 10 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$	2N3772			2.2	
(I <sub>C</sub> = 8.0 Adc, V <sub>CE</sub> = 4.0 Vdc)					
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product		f <sub>T</sub>	0.2	_	MHz
$(I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f_{test} = 50 \text{ kHz})$					
Small–Signal Current Gain		h <sub>fe</sub>	40	_	-
(I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 4.0 Vdc, f = 1.0 kHz)					
ECOND BREAKDOWN					
Second Breakdown Energy with Base Forward Biased, t = 1.0 s (no		I <sub>S/b</sub>			Adc
(V <sub>CE</sub> = 40 Vdc) (V <sub>CE</sub> = 60 Vdc)	2N3771 2N3772		3.75	-	
			2.5		

\*Indicates JEDEC Registered Data. (1) Pulse Test: 300 s, Rep. Rate 60 cps.







# **TYPICAL CHARACTERISTICS CURVES**



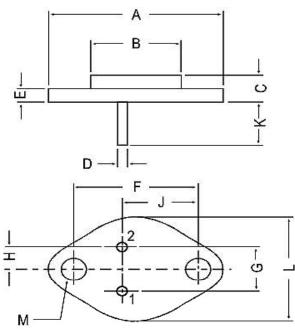


#### 100 2000 T<sub>J</sub> = 25YC 50 V<sub>CC</sub> = 30 V $I_{\rm C}/I_{\rm B}=10$ 20 $I_{B1} = I_{B2}$ C, CAPACITANCE (pF) 002 001 001 T<sub>J</sub> = 25)C Cit 10 ŝ Cob 5.0 t, TIME ( 2.0 1.0 tr 0.5 300 0.2 0.1 200 0.5 0.3 2.0 3.0 5.0 7.0 20 30 0.2 1.0 10 0.1 0.5 1.0 2.0 5.0 10 20 50 100 IC, COLLECTOR CURRENT (AMP) V<sub>R</sub>, REVERSE VOLTAGE (VOLTS) Figure 6. Turn-Off Time Figure 7. Capacitance 500 COLLECTOR-EMITTER VOLTAGE (VOLTS) 2.0 T<sub>J</sub> = 25)C 300 T<sub>J</sub> = 1501C V<sub>CE</sub> = 4.0 V 200 1.6 I<sub>C</sub> = 2.0 A 25)C 5.0 A 10 A 20 A hFE, DC CURRENT GAIN -----100 1.2 70 50 -55)C 0.8 30 20 0.4 10 7.0 VCE, 5.0 C 0.01 0.5 0.7 1.0 2.0 3.0 10 20 30 5.0 7.0 0.02 2.0 0.05 0.1 0.2 0.5 1.0 5.0 10 IC, COLLECTOR CURRENT (AMP) IC, COLLECTOR CURRENT (AMP) Figure 9. Collector Saturation Region Figure 8. DC Current Gain

# TYPICAL CHARACTERISTICS CURVES



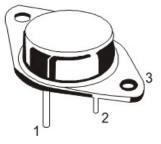
# **Package Details**





_			
	DIM	MIN.	MAX.
	А		39.37
	В	_	22.22
	С	6.35	8.50
	D	0.96	1.09
	Е	-	1.77
	F	29.90	30.40
	G	10.69	11.18
	Н	5.20	5.72
	J	16.64	17.15
	К	11.15	12.25
	L		26.67
	М	3.84	4.19

All dimensions in mm.



**PIN CONFIGURATION** 

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

# **Packing Detail**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-3	100 pcs/pkt	1.3 kg/100 pcs	12.5" x 8" x 1.8"	0.1K	17" x 11.5" x 21"	2K	27.5 kgs





# Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- $\cdot\,$  Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- · Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- $\cdot\,$  Mechanical stress such as vibration and impact shall be avoided.
- $\cdot\,$  The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

## **Shelf Life of CDIL Products**

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

### Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level					
Level	Time	Condition			
1	Unlimited	≤30 °C / 85% RH			
2	1 Year	≤30 °C / 60% RH			
2a	4 Weeks	≤30 °C / 60% RH			
3	168 Hours	≤30 °C / 60% RH			
4	72 Hours	≤30 °C / 60% RH			
5	48 Hours	≤30 °C / 60% RH			
5a	24 Hours	≤30 °C / 60% RH			
6	Time on Label(TOL)	≤30 °C / 60% RH			



## **Customer Notes**

## **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

## Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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